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RELIABILITY REPORT
FOR

DS1834, Rev A3

Dallas Semiconductor

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Conclusion:

The following qualification successfully meets the quality and reliability standards required of all Dallas Semiconductor products and processes:

DS1834, Rev A3

In addition, Dallas Semiconductor's continuous reliability monitor program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards. The current status of the reliability monitor program can be viewed at http://www.maxim-ic.com/TechSupport /dsreliability.html.

Device Description:

A description of this device can be found in the product data sheet. You can find the product data sheet at http://dbserv.maxim-ic.com/l_datasheet3.cfm.

Reliability Derating:

The Arrhenius model will be used to determine the acceleration factor for failure mechanisms that are temperature accelerated.

AfT = exp((Ea/k)*(1/Tu - 1/Ts)) = tu/ts
AfT = Acceleration factor due to Temperature
tu = Time at use temperature (e.g. 55°C)
ts = Time at stress temperature (e.g. 125°C)
k = Boltzmann's Constant (8.617 x 10-5 eV/°K)
Tu = Temperature at Use (°K)
Ts = Temperature at Stress (°K)
Ea = Activation Energy (e.g. 0.7 ev)

The activation energy of the failure mechanism is derived from either internal studies or industry accepted standards, or activation energy of 0.7ev will be used whenever actual failure mechanisms or their activation energies are unknown. All deratings will be done from the stress ambient temperature to the use ambient temperature.

An exponential model will be used to determine the acceleration factor for failure mechanisms, which are voltage accelerated.

AfV = exp(B*(Vs - Vu))
AfV = Acceleration factor due to Voltage
Vs = Stress Voltage (e.g. 7.0 volts)
Vu = Maximum Operating Voltage (e.g. 5.5 volts)
B = Constant related to failure mechanism type (e.g. 1.0, 2.4, 2.7, etc.)

The Constant, B, related to the failure mechanism is derived from either internal studies or industry accepted standards, or a B of 1.0 will be used whenever actual failure mechanisms or their B are unknown. All deratings will be done from the stress voltage to the maximum operating voltage. Failure rate data from the operating life test is reported using a Chi-Squared statistical model at the 60% or 90% confidence level (Cf).

The failure rate, Fr, is related to the acceleration during life test by:

Fr = X/(ts * AfV * AfT * N * 2)
X = Chi-Sq statistical upper limit
N = Life test sample size

Failure Rates are reported in FITs (Failures in Time) or MTTF (Mean Time To Failure). The FIT rate is related to MTTF by:

MTTF = 1/Fr

NOTE: MTTF is frequently used interchangeably with MTBF.

The calculated failure rate for this device/process is:

FAILURE RATE: MTTF (YRS): 84548 FITS: 1.4

The parameters used to calculate this failure rate are as follows:

Cf: 60% Ea: 0.7 B: 0 Tu: 25 °C Vu: 5.5 Volts

The reliability data follows. A the start of this data is the device information. The next section is the detailed reliability data for each stress. The reliability data section includes the latest data available.

Device Information:

Process:	1P, 1M, 0.8um,Neg ZTC P1R,PdplD,Low Vts,BPSG ILO, N+ESDII,
Passivation:	Passivation w/Nov TEOS Oxide-Nitride
Die Size:	46 x 61
Number of Transistors:	0
Interconnect:	Aluminum / 1% Silicon / 0.5% Copper
Gate Oxide Thickness:	175 Å

ELECTRICAL CHARACTERIZATION

DESCRIPTION	DATE CODE	CONDITION	READPOINT		QUANTITY	FAILS
ESD SENSITIVITY	0218	EOS/ESD S5.1 HBM 500 VOLTS	2	PUL'S	3	0
ESD SENSITIVITY	0218	EOS/ESD S5.1 HBM 1000 VOLTS	1	PUL'S	3	0
ESD SENSITIVITY	0218	EOS/ESD S5.1 HBM 2000 VOLTS	1	PUL'S	3	0
ESD SENSITIVITY	0218	EOS/ESD S5.1 HBM 4000 VOLTS	1	PUL'S	3	0
ESD SENSITIVITY	0218	EOS/ESD S5.1 HBM 8000 VOLTS	1	PUL'S	3	3
LATCH-UP	0218	JESD78, I-TEST 125C			3	0
LATCH-UP	0218	JESD78, Vsupply TEST 125C			3	0
				Total:		**3**

OPERATING LIFE

DESCRIPTION	DATE CODE	CONDITION	READPOINT		QUANTITY	FAILS
INFANT LIFE	0012	125C, 7.0 VOLTS	48	HRS	144	0
HIGH VOLTAGE LIFE	0012	125C, 7.0 VOLTS	1000	HRS	72	0
INFANT LIFE	0013	125C, 7.0 VOLTS	48	HRS	144	0
HIGH VOLTAGE LIFE	0013	125C, 7.0 VOLTS	1000	HRS	72	0
INFANT LIFE	0014	125C, 7.0 VOLTS	48	HRS	186	0
HIGH VOLTAGE LIFE	0014	125C, 7.0 VOLTS	1000	HRS	114	0
INFANT LIFE	0029	125C, 7.0 VOLTS	48	HRS	183	0
HIGH VOLTAGE LIFE	0029	125C, 7.0 VOLTS	1000	HRS	114	0

HIGH VOLTAGE LIFE	0147	125C, 6.0 VOLTS	1000	HRS	80	0
HIGH VOLTAGE LIFE	0210	125C, 7.0 VOLTS	1000	HRS	78	0
HIGH VOLTAGE LIFE	0218	125C, 6.0 VOLTS	1000	HRS	80	0
HIGH VOLTAGE LIFE	0222	125C, 7.0 VOLTS	1000	HRS	78	0
				Total:		**0**

TEMPERATURE CYCLE

DESCRIPTION	DATE CODE	CONDITION	READPOINT		QUANTITY	FAILS
TEMP CYCLE	0012	-55C TO 125C	1000	CYS	77	0
TEMP CYCLE	0013	-55C TO 125C	1000	CYS	77	0
TEMP CYCLE	0014	-55C TO 125C	1000	CYS	77	0
TEMP CYCLE	0029	-55C TO 125C	1000	CYS	77	0
TEMP CYCLE	0222	-55C TO 125C	1000	CYS	77	0
				Total:		**0**

TEMPERATURE HUMIDITY BIAS

DESCRIPTION	DATE CODE	CONDITION	READPOINT		QUANTITY	FAILS
BIASED MOISTURE	0012	85/85, 5.5 VOLTS	959	HRS	72	0
BIASED MOISTURE	0013	85/85, 5.5 VOLTS	959	HRS	72	0
BIASED MOISTURE	0014	85/85, 5.5 VOLTS	959	HRS	72	0
BIASED MOISTURE	0029	85/85, 5.5 VOLTS	959	HRS	75	0
BIASED MOISTURE	0222	85/85, 5.5 VOLTS	959	HRS	78	0
				Total:		**0**

UNBIASED MOISTURE RESISTANCE

DESCRIPTION	DATE CODE	CONDITION	READPOINT		QUANTITY	FAILS
AUTOCLAVE	0012	121C, 2 ATM STEAM, UNBIASED	168	HRS	45	0
AUTOCLAVE	0013	121C, 2 ATM STEAM, UNBIASED	168	HRS	45	0
AUTOCLAVE	0014	121C, 2 ATM STEAM, UNBIASED	168	HRS	45	0
AUTOCLAVE	0029	121C, 2 ATM STEAM, UNBIASED	168	HRS	45	0
AUTOCLAVE	0222	121C, 2 ATM STEAM, UNBIASED	168	HRS	76	0
				Total:		**0**

FAILURE RATE: **MTTF (YRS): 84548** **FITS: 1.4**